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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	HDMI-CEC, I²C, IrDA, LINbus, SPI, UART/USART
Peripherals	DMA, I²S, POR, PWM, WDT
Number of I/O	37
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.65V ~ 3.6V
Data Converters	A/D 13x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-UFQFN Exposed Pad
Supplier Device Package	48-UFQFPN (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f071cbu6tr

Table 2. STM32F071x8/xB family device features and peripheral counts

Peripheral		STM32F071Cx		STM32F071RB	STM32F071Vx	
Flash memory (Kbyte)		64	128	128	64	128
SRAM (Kbyte)		16				
Timers	Advanced control	1 (16-bit)				
	General purpose	5 (16-bit) 1 (32-bit)				
	Basic	2 (16-bit)				
Comm. interfaces	SPI [I^2S](1)	2 [2]				
	I^2C	2				
	USART	4				
	CEC	1				
12-bit ADC (number of channels)		1 (10 ext. + 3 int.)		1 (16 ext. + 3 int.)		
12-bit DAC (number of channels)		1 (2)				
Analog comparator		2				
GPIOs		37		51	87	
Capacitive sensing channels		17		18	24	
Max. CPU frequency		48 MHz				
Operating voltage		2.0 to 3.6 V				
Operating temperature		Ambient operating temperature: -40°C to 85°C / -40°C to 105°C Junction temperature: -40°C to 105°C / -40°C to 125°C				
Packages		LQFP48 UFQFPN48 WLCSP49		LQFP64	LQFP100 UFBGA100	

1. The SPI interface can be used either in SPI mode or in I^2S audio mode.

3 Functional overview

Figure 1 shows the general block diagram of the STM32F071x8/xB devices.

3.1 ARM®-Cortex®-M0 core

The ARM® Cortex®-M0 is a generation of ARM 32-bit RISC processors for embedded systems. It has been developed to provide a low-cost platform that meets the needs of MCU implementation, with a reduced pin count and low-power consumption, while delivering outstanding computational performance and an advanced system response to interrupts.

The ARM® Cortex®-M0 processors feature exceptional code-efficiency, delivering the high performance expected from an ARM core, with memory sizes usually associated with 8- and 16-bit devices.

The STM32F071x8/xB devices embed ARM core and are compatible with all ARM tools and software.

3.2 Memories

The device has the following features:

- 16 Kbytes of embedded SRAM accessed (read/write) at CPU clock speed with 0 wait states and featuring embedded parity checking with exception generation for fail-critical applications.
- The non-volatile memory is divided into two arrays:
  - 64 to 128 Kbytes of embedded Flash memory for programs and data
  - Option bytes

  The option bytes are used to write-protect the memory (with 4 KB granularity) and/or readout-protect the whole memory with the following options:
  - Level 0: no readout protection
  - Level 1: memory readout protection, the Flash memory cannot be read from or written to if either debug features are connected or boot in RAM is selected
  - Level 2: chip readout protection, debug features (Cortex®-M0 serial wire) and boot in RAM selection disabled

3.3 Boot modes

At startup, the boot pin and boot selector option bit are used to select one of the three boot options:

- boot from User Flash memory
- boot from System Memory
- boot from embedded SRAM

The boot loader is located in System Memory. It is used to reprogram the Flash memory by using USART on pins PA14/PA15, or PA9/PA10 or I^2C on pins PB6/PB7.

TIM15 has two independent channels, whereas TIM16 and TIM17 feature one single channel for input capture/output compare, PWM or one-pulse mode output.

The TIM15, TIM16 and TIM17 timers can work together, and TIM15 can also operate withTIM1 via the Timer Link feature for synchronization or event chaining.

TIM15 can be synchronized with TIM16 and TIM17.

TIM15, TIM16 and TIM17 have a complementary output with dead-time generation and independent DMA request generation.

Their counters can be frozen in debug mode.

3.14.3 Basic timers TIM6 and TIM7

These timers are mainly used for DAC trigger generation. They can also be used as generic 16-bit time bases.

3.14.4 Independent watchdog (IWDG)

The independent watchdog is based on an 8-bit prescaler and 12-bit downcounter with user-defined refresh window. It is clocked from an independent 40 kHz internal RC and as it operates independently from the main clock, it can operate in Stop and Standby modes. It can be used either as a watchdog to reset the device when a problem occurs, or as a free running timer for application timeout management. It is hardware or software configurable through the option bytes. The counter can be frozen in debug mode.

3.14.5 System window watchdog (WWDG)

The system window watchdog is based on a 7-bit downcounter that can be set as free running. It can be used as a watchdog to reset the device when a problem occurs. It is clocked from the APB clock (PCLK). It has an early warning interrupt capability and the counter can be frozen in debug mode.

3.14.6 SysTick timer

This timer is dedicated to real-time operating systems, but could also be used as a standard down counter. It features:

- a 24-bit down counter
- autoreload capability
- maskable system interrupt generation when the counter reaches 0
- programmable clock source (HCLK or HCLK/8)

3.15 Real-time clock (RTC) and backup registers

The RTC and the five backup registers are supplied through a switch that takes power either on V_{DD} supply when present or through the V_{BAT} pin. The backup registers are five 32-bit registers used to store 20 bytes of user application data when V_{DD} power is not present. They are not reset by a system or power reset, or at wake up from Standby mode.

6 Electrical characteristics

6.1 Parameter conditions

Unless otherwise specified, all voltages are referenced to V_{SS}.

6.1.1 Minimum and maximum values

Unless otherwise specified, the minimum and maximum values are guaranteed in the worst conditions of ambient temperature, supply voltage and frequencies by tests in production on 100% of the devices with an ambient temperature at T_A = 25 °C and T_A = $T_A$max (given by the selected temperature range).

Data based on characterization results, design simulation and/or technology characteristics are indicated in the table footnotes and are not tested in production. Based on characterization, the minimum and maximum values refer to sample tests and represent the mean value plus or minus three times the standard deviation (mean ±3σ).

6.1.2 Typical values

Unless otherwise specified, typical data are based on T_A = 25 °C, V_{DD} = V_{DDA} = 3.3 V. They are given only as design guidelines and are not tested.

Typical ADC accuracy values are determined by characterization of a batch of samples from a standard diffusion lot over the full temperature range, where 95% of the devices have an error less than or equal to the value indicated (mean ±2σ).

6.1.3 Typical curves

Unless otherwise specified, all typical curves are given only as design guidelines and are not tested.

6.1.4 Loading capacitor

The loading conditions used for pin parameter measurement are shown in *Figure 10*.

6.1.5 Pin input voltage

The input voltage measurement on a pin of the device is described in *Figure 11*.

Figure 10. Pin loading conditions

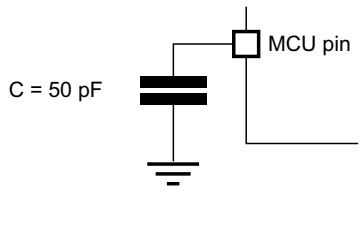


Figure 11. Pin input voltage

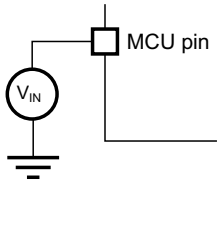


Table 25. Operating conditions at power-up / power-down

Symbol	Parameter	Conditions	Min	Max	Unit
t_{VDD}	V_{DD} rise time rate	-	0	∞	µs/V
	V_{DD} fall time rate		20	∞	
t_{VDDA}	V_{DDA} rise time rate	-	0	∞	
	V_{DDA} fall time rate		20	∞	

6.3.3 Embedded reset and power control block characteristics

The parameters given in *Table 26* are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 24: General operating conditions*.

Table 26. Embedded reset and power control block characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{POR/PDR}$(1)	Power on/power down reset threshold	Falling edge(2)	1.80	1.88	1.96(3)	V
		Rising edge	1.84(3)	1.92	2.00	V
$V_{PDRhyst}$	PDR hysteresis	-	-	40	-	mV
$t_{RSTTEMPO}$(4)	Reset temporization	-	1.50	2.50	4.50	ms

1. The PDR detector monitors V_{DD} and also V_{DDA} (if kept enabled in the option bytes). The POR detector monitors only V_{DD}.
2. The product behavior is guaranteed by design down to the minimum $V_{POR/PDR}$ value.
3. Data based on characterization results, not tested in production.
4. Guaranteed by design, not tested in production.

Table 27. Programmable voltage detector characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{PVD0}	PVD threshold 0	Rising edge	2.1	2.18	2.26	V
		Falling edge	2	2.08	2.16	V
V_{PVD1}	PVD threshold 1	Rising edge	2.19	2.28	2.37	V
		Falling edge	2.09	2.18	2.27	V
V_{PVD2}	PVD threshold 2	Rising edge	2.28	2.38	2.48	V
		Falling edge	2.18	2.28	2.38	V
V_{PVD3}	PVD threshold 3	Rising edge	2.38	2.48	2.58	V
		Falling edge	2.28	2.38	2.48	V
V_{PVD4}	PVD threshold 4	Rising edge	2.47	2.58	2.69	V
		Falling edge	2.37	2.48	2.59	V
V_{PVD5}	PVD threshold 5	Rising edge	2.57	2.68	2.79	V
		Falling edge	2.47	2.58	2.69	V

Typical and maximum current consumption

The MCU is placed under the following conditions:

- All I/O pins are in analog input mode
- All peripherals are disabled except when explicitly mentioned
- The Flash memory access time is adjusted to the f_{HCLK} frequency:
  - 0 wait state and Prefetch OFF from 0 to 24 MHz
  - 1 wait state and Prefetch ON above 24 MHz
- When the peripherals are enabled $f_{PCLK} = f_{HCLK}$

The parameters given in to *Table 31* are derived from tests performed under ambient temperature and supply voltage conditions summarized in *Table 24: General operating conditions*.

Table 29. Typical and maximum current consumption from V_{DD} supply at V_{DD} = 3.6 V

Symbol	Parameter	Conditions	f_{HCLK}	All peripherals enabled				All peripherals disabled				Unit
				Typ	Max @ T_A(1)			Typ	Max @ T_A(1)			
					25 °C	85 °C	105 °C		25 °C	85 °C	105 °C	
I_{DD}	Supply current in Run mode, code executing from Flash memory	HSI48	48 MHz	24.3	26.9	27.2	27.9	13.1	14.8	14.9	15.5	mA
		HSE bypass, PLL on	48 MHz	24.1	26.8	27.0	27.7	13.0	14.6	14.8	15.4	
			32 MHz	16.0	18.3	18.6	19.2	8.76	9.56	9.73	10.6	
			24 MHz	12.3	13.7	14.3	14.7	7.36	7.94	8.37	8.81	
		HSE bypass, PLL off	8 MHz	4.52	5.25	5.28	5.61	2.89	3.17	3.26	3.34	
			1 MHz	1.25	1.39	1.58	1.87	0.93	1.06	1.15	1.34	
		HSI clock, PLL on	48 MHz	24.1	27.1	27.6	27.8	12.9	14.7	14.9	15.5	
			32 MHz	16.1	18.2	18.9	19.3	8.82	9.69	9.83	10.7	
			24 MHz	12.4	14.0	14.4	14.8	7.31	7.92	8.34	8.75	
		HSI clock, PLL off	8 MHz	4.52	5.25	5.35	5.61	2.87	3.16	3.25	3.33	

Table 30. Typical and maximum current consumption from the V_{DDA} supply

Symbol	Para-meter	Conditions (1)	f_{HCLK}	V_{DDA} = 2.4 V				V_{DDA} = 3.6 V				Unit
				Typ	Max @ T_A(2)			Typ	Max @ T_A(2)			
					25 °C	85 °C	105 °C		25 °C	85 °C	105 °C	
I_{DDA}	Supply current in Run or Sleep mode, code executing from Flash memory or RAM	HSI48	48 MHz	311	326	334	343	322	337	345	354	µA
		HSE bypass, PLL on	48 MHz	152	170(3)	178	182(3)	165	184(3)	196	200(3)	
			32 MHz	105	121	126	128	113	129	136	138	
			24 MHz	81.9	95.9	99.5	101	88.7	102	107	108	
		HSE bypass, PLL off	8 MHz	2.7	3.8	4.3	4.6	3.6	4.7	5.2	5.5	
			1 MHz	2.7	3.8	4.3	4.6	3.6	4.7	5.2	5.5	
		HSI clock, PLL on	48 MHz	223	244	255	260	245	265	279	284	
			32 MHz	176	195	203	206	193	212	221	224	
			24 MHz	154	171	178	181	168	185	192	195	
		HSI clock, PLL off	8 MHz	74.2	83.4	86.4	87.3	83.4	92.5	95.3	96.6	

1. Current consumption from the V_{DDA} supply is independent of whether the digital peripherals are enabled or disabled, being in Run or Sleep mode or executing from Flash memory or RAM. Furthermore, when the PLL is off, I_{DDA} is independent from the frequency.
2. Data based on characterization results, not tested in production unless otherwise specified.
3. Data based on characterization results and tested in production (using one common test limit for sum of I_{DD} and I_{DDA}).

Table 32. Typical and maximum current consumption from the V_{BAT} supply

Symbol	Parameter	Conditions	Typ @ V_{BAT}						Max(1)			Unit
			1.65 V	1.8 V	2.4 V	2.7 V	3.3 V	3.6 V	T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	
I_{DD_VBAT}	RTC domain supply current	LSE & RTC ON; “Xtal mode”: lower driving capability; LSEDRV[1:0] = '00'	0.5	0.6	0.7	0.8	1.1	1.2	1.3	1.7	2.3	µA
		LSE & RTC ON; “Xtal mode” higher driving capability; LSEDRV[1:0] = '11'	0.8	0.9	1.1	1.2	1.4	1.6	1.7	2.1	2.8	

1. Data based on characterization results, not tested in production.

Typical current consumption

The MCU is placed under the following conditions:

- $V_{DD} = V_{DDA} = 3.3$ V
- All I/O pins are in analog input configuration
- The Flash memory access time is adjusted to f_{HCLK} frequency:
  - 0 wait state and Prefetch OFF from 0 to 24 MHz
  - 1 wait state and Prefetch ON above 24 MHz
- When the peripherals are enabled, $f_{PCLK} = f_{HCLK}$
- PLL is used for frequencies greater than 8 MHz
- AHB prescaler of 2, 4, 8 and 16 is used for the frequencies 4 MHz, 2 MHz, 1 MHz and 500 kHz respectively

trigger circuits used to discriminate the input value. Unless this specific configuration is required by the application, this supply current consumption can be avoided by configuring these I/Os in analog mode. This is notably the case of ADC input pins which should be configured as analog inputs.

Caution: Any floating input pin can also settle to an intermediate voltage level or switch inadvertently, as a result of external electromagnetic noise. To avoid current consumption related to floating pins, they must either be configured in analog mode, or forced internally to a definite digital value. This can be done either by using pull-up/down resistors or by configuring the pins in output mode.

I/O dynamic current consumption

In addition to the internal peripheral current consumption measured previously (see *Table 35: Peripheral current consumption*), the I/Os used by an application also contribute to the current consumption. When an I/O pin switches, it uses the current from the I/O supply voltage to supply the I/O pin circuitry and to charge/discharge the capacitive load (internal or external) connected to the pin:

$$I_{SW} = V_{DDIOx} \times f_{SW} \times C$$

where

I_{SW} is the current sunk by a switching I/O to charge/discharge the capacitive load

V_{DDIOx} is the I/O supply voltage

f_{SW} is the I/O switching frequency

C is the total capacitance seen by the I/O pin: $C = C_{INT} + C_{EXT} + C_S$

C_S is the PCB board capacitance including the pad pin.

The test pin is configured in push-pull output mode and is toggled by software at a fixed frequency.

On-chip peripheral current consumption

The current consumption of the on-chip peripherals is given in *Table 35*. The MCU is placed under the following conditions:

- All I/O pins are in analog mode
- All peripherals are disabled unless otherwise mentioned
- The given value is calculated by measuring the current consumption
  - with all peripherals clocked off
  - with only one peripheral clocked on
- Ambient operating temperature and supply voltage conditions summarized in *Table 21: Voltage characteristics*
- The power consumption of the digital part of the on-chip peripherals is given in *Table 35*. The power consumption of the analog part of the peripherals (where applicable) is indicated in each related section of the datasheet.

Table 35. Peripheral current consumption

Peripheral		Typical consumption at 25 °C	Unit
AHB	BusMatrix(1)	2.2	µA/MHz
	CRC	1.6	
	DMA	5.7	
	Flash memory interface	13.0	
	GPIOA	8.2	
	GPIOB	8.5	
	GPIOC	2.3	
	GPIOD	1.9	
	GPIOE	2.2	
	GPIOF	1.2	
	SRAM	0.9	
	TSC	5.0	
	All AHB peripherals	**52.6**	

6.3.6 Wakeup time from low-power mode

The wakeup times given in *Table 36* are the latency between the event and the execution of the first user instruction. The device goes in low-power mode after the WFE (Wait For Event) instruction, in the case of a WFI (Wait For Interruption) instruction, 16 CPU cycles must be added to the following timings due to the interrupt latency in the Cortex M0 architecture.

The SYSCLK clock source setting is kept unchanged after wakeup from Sleep mode. During wakeup from Stop or Standby mode, SYSCLK takes the default setting: HSI 8 MHz.

The wakeup source from Sleep and Stop mode is an EXTI line configured in event mode. The wakeup source from Standby mode is the WKUP1 pin (PA0).

All timings are derived from tests performed under the ambient temperature and supply voltage conditions summarized in *Table 24: General operating conditions*.

Table 36. Low-power mode wakeup timings

Symbol	Parameter	Conditions	Typ @V_{DD} = V_{DDA}					Max	Unit
			= 2.0 V	= 2.4 V	= 2.7 V	= 3 V	= 3.3 V		
t_{WUSTOP}	Wakeup from Stop mode	Regulator in run mode	3.2	3.1	2.9	2.9	2.8	5	µs
		Regulator in low power mode	7.0	5.8	5.2	4.9	4.6	9	
$t_{WUSTANDBY}$	Wakeup from Standby mode	-	60.4	55.6	53.5	52	51	-	
$t_{WUSLEEP}$	Wakeup from Sleep mode	-	4 SYSCLK cycles					-	

6.3.7 External clock source characteristics

High-speed external user clock generated from an external source

In bypass mode the HSE oscillator is switched off and the input pin is a standard GPIO.

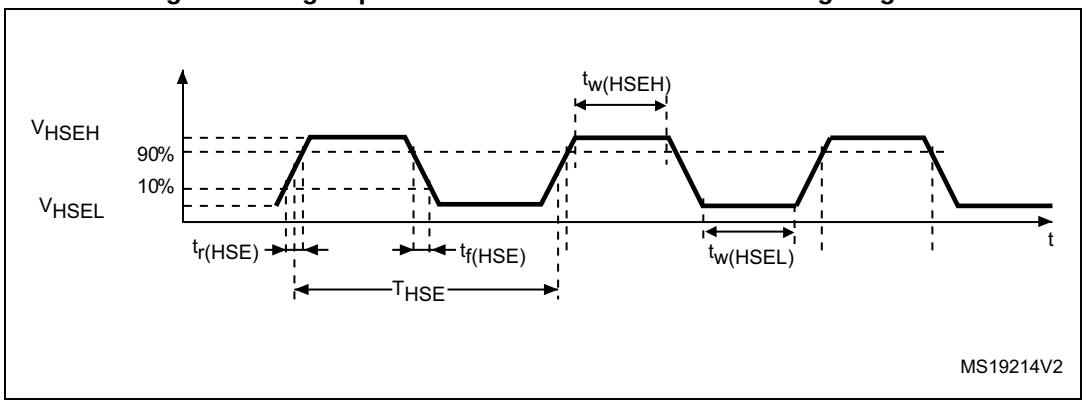
The external clock signal has to respect the I/O characteristics in *Section 6.3.14*. However, the recommended clock input waveform is shown in *Figure 14: High-speed external clock source AC timing diagram*.

Table 37. High-speed external user clock characteristics

Symbol	Parameter[1]	Min	Typ	Max	Unit
f_{HSE_ext}	User external clock source frequency	-	8	32	MHz
V_{HSEH}	OSC_IN input pin high level voltage	0.7 V_{DDIOx}	-	V_{DDIOx}	V
V_{HSEL}	OSC_IN input pin low level voltage	V_{SS}	-	0.3 V_{DDIOx}	
$t_{w(HSEH)}$ $t_{w(HSEL)}$	OSC_IN high or low time	15	-	-	ns
$t_{r(HSE)}$ $t_{f(HSE)}$	OSC_IN rise or fall time	-	-	20	

1. Guaranteed by design, not tested in production.

Figure 14. High-speed external clock source AC timing diagram



Low-speed external user clock generated from an external source

In bypass mode the LSE oscillator is switched off and the input pin is a standard GPIO.

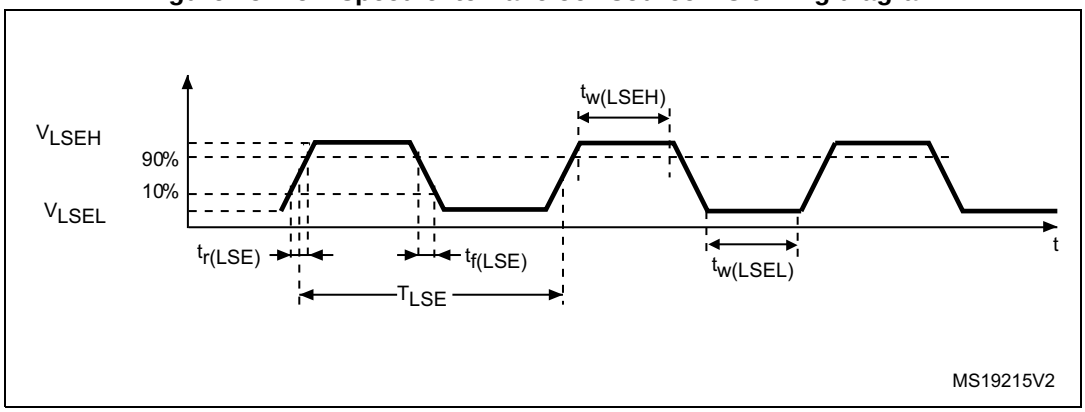
The external clock signal has to respect the I/O characteristics in *Section 6.3.14*. However, the recommended clock input waveform is shown in *Figure 15*.

Table 38. Low-speed external user clock characteristics

Symbol	Parameter(1)	Min	Typ	Max	Unit
f_{LSE_ext}	User external clock source frequency	-	32.768	1000	kHz
V_{LSEH}	OSC32_IN input pin high level voltage	0.7 V_{DDIOx}	-	V_{DDIOx}	V
V_{LSEL}	OSC32_IN input pin low level voltage	V_{SS}	-	0.3 V_{DDIOx}	
$t_{w(LSEH)}$ $t_{w(LSEL)}$	OSC32_IN high or low time	450	-	-	ns
$t_{r(LSE)}$ $t_{f(LSE)}$	OSC32_IN rise or fall time	-	-	50	

1. Guaranteed by design, not tested in production.

Figure 15. Low-speed external clock source AC timing diagram



Low-speed internal (LSI) RC oscillator

Table 44. LSI oscillator characteristics(1)

Symbol	Parameter	Min	Typ	Max	Unit
f_{LSI}	Frequency	30	40	50	kHz
$t_{su(LSI)}$(2)	LSI oscillator startup time	-	-	85	µs
$I_{DDA(LSI)}$(2)	LSI oscillator power consumption	-	0.75	1.2	µA

1. V_{DDA} = 3.3 V, T_A = –40 to 105 °C unless otherwise specified.
2. Guaranteed by design, not tested in production.

6.3.9 PLL characteristics

The parameters given in *Table 45* are derived from tests performed under ambient temperature and supply voltage conditions summarized in *Table 24: General operating conditions*.

Table 45. PLL characteristics

Symbol	Parameter	Value			Unit
		Min	Typ	Max	
f_{PLL_IN}	PLL input clock(1)	1(2)	8.0	24(2)	MHz
	PLL input clock duty cycle	40(2)	-	60(2)	%
f_{PLL_OUT}	PLL multiplier output clock	16(2)	-	48	MHz
t_{LOCK}	PLL lock time	-	-	200(2)	µs
$Jitter_{PLL}$	Cycle-to-cycle jitter	-	-	300(2)	ps

1. Take care to use the appropriate multiplier factors to obtain PLL input clock values compatible with the range defined by f_{PLL_OUT}.
2. Guaranteed by design, not tested in production.

6.3.10 Memory characteristics

Flash memory

The characteristics are given at T_A = –40 to 105 °C unless otherwise specified.

Table 46. Flash memory characteristics

Symbol	Parameter	Conditions	Min	Typ	Max(1)	Unit
t_{prog}	16-bit programming time	T_A = - 40 to +105 °C	40	53.5	60	µs
t_{ERASE}	Page (2 KB) erase time	T_A = - 40 to +105 °C	20	-	40	ms
t_{ME}	Mass erase time	T_A = - 40 to +105 °C	20	-	40	ms
I_{DD}	Supply current	Write mode	-	-	10	mA
		Erase mode	-	-	12	mA

1. Guaranteed by design, not tested in production.

2. ADC Accuracy vs. Negative Injection Current: Injecting negative current on any of the standard (non-robust) analog input pins should be avoided as this significantly reduces the accuracy of the conversion being performed on another analog input. It is recommended to add a Schottky diode (pin to ground) to standard analog pins which may potentially inject negative current.
Any positive injection current within the limits specified for $I_{INJ(PIN)}$ and $\Sigma I_{INJ(PIN)}$ in *Section 6.3.14* does not affect the ADC accuracy.
3. Better performance may be achieved in restricted V_{DDA}, frequency and temperature ranges.
4. Data based on characterization results, not tested in production.

Figure 25. ADC accuracy characteristics

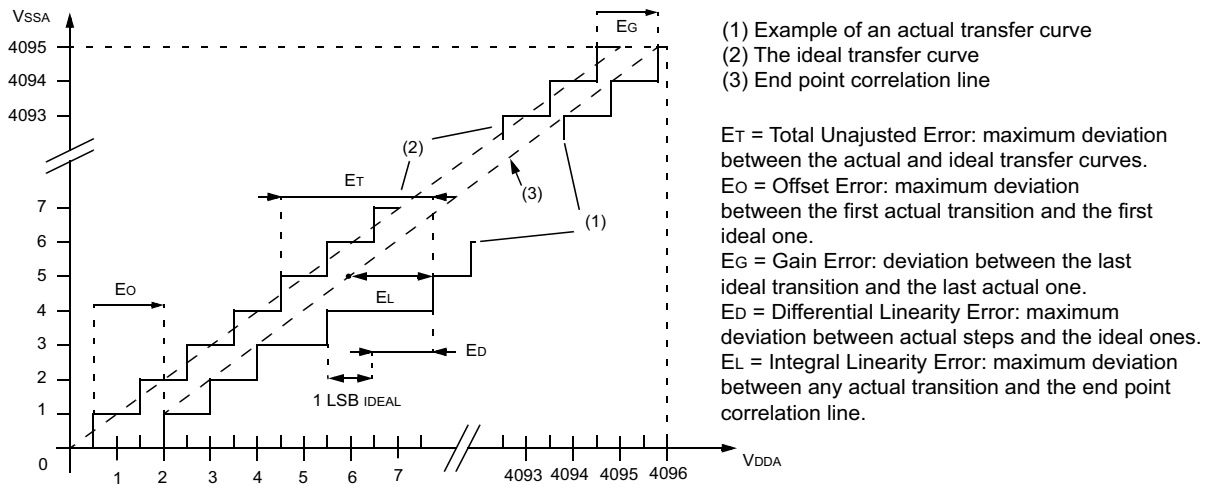
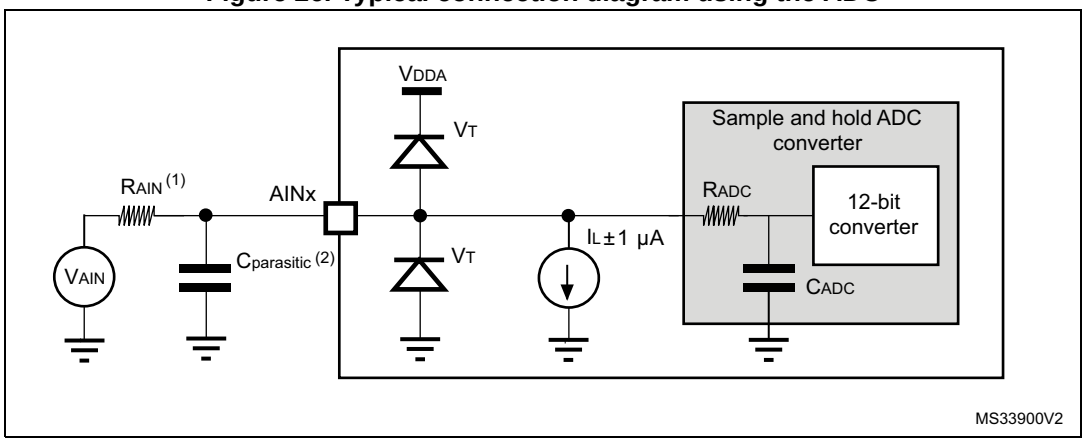


Figure 26. Typical connection diagram using the ADC



1. Refer to *Table 57: ADC characteristics* for the values of R_{AIN}, R_{ADC} and C_{ADC}.
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high $C_{parasitic}$ value will downgrade conversion accuracy. To remedy this, f_{ADC} should be reduced.

General PCB design guidelines

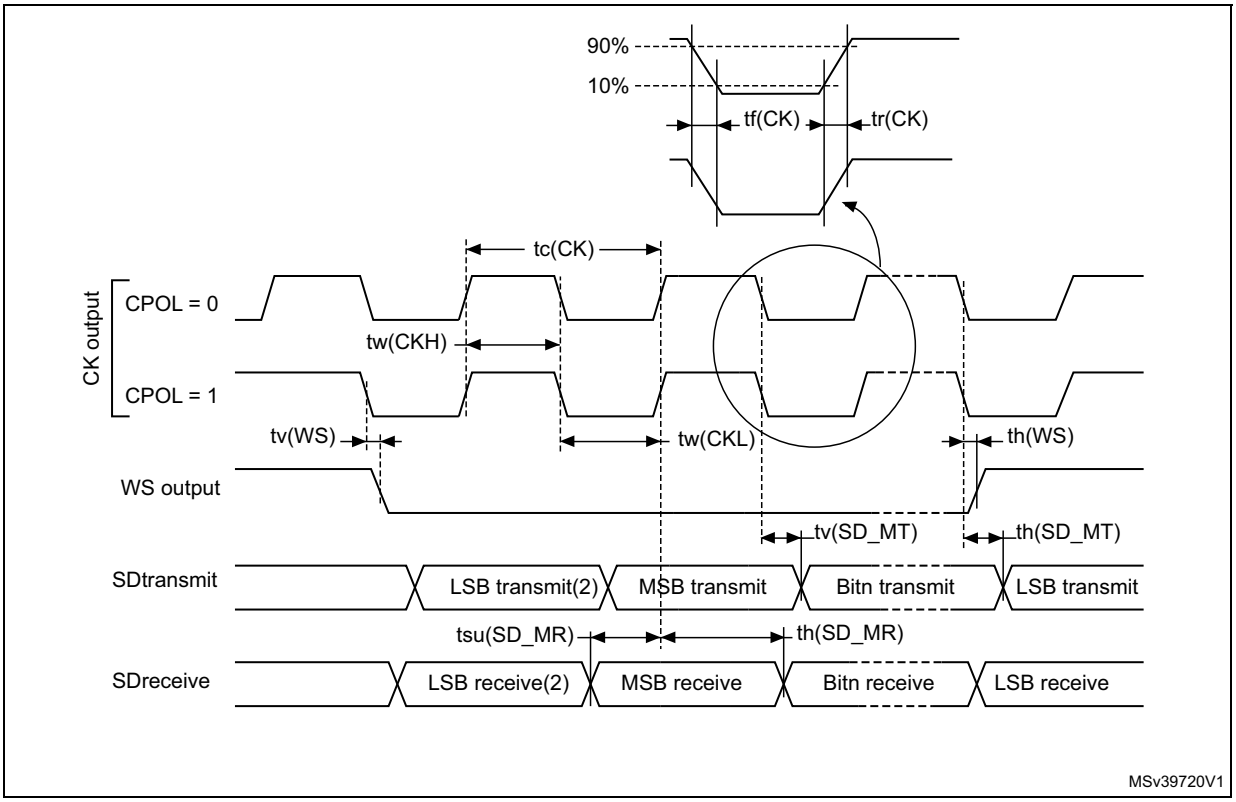
Power supply decoupling should be performed as shown in *Figure 12: Power supply scheme*. The 10 nF capacitor should be ceramic (good quality) and it should be placed as close as possible to the chip.

6.3.17 DAC electrical specifications

Table 60. DAC characteristics

Symbol	Parameter	Min	Typ	Max	Unit	Comments
V_{DDA}	Analog supply voltage for DAC ON	2.4	-	3.6	V	-
R_{LOAD}(1)	Resistive load with buffer ON	5	-	-	kΩ	Load connected to V_{SSA}
		25	-	-	kΩ	Load connected to V_{DDA}
R_O(1)	Impedance output with buffer OFF	-	-	15	kΩ	When the buffer is OFF, the Minimum resistive load between DAC_OUT and V_{SS} to have a 1% accuracy is 1.5 MΩ
C_{LOAD}(1)	Capacitive load	-	-	50	pF	Maximum capacitive load at DAC_OUT pin (when the buffer is ON).
DAC_OUT min(1)	Lower DAC_OUT voltage with buffer ON	0.2	-	-	V	It gives the maximum output excursion of the DAC. It corresponds to 12-bit input code (0x0E0) to (0xF1C) at V_{DDA} = 3.6 V and (0x155) and (0xEAB) at V_{DDA} = 2.4 V
DAC_OUT max(1)	Higher DAC_OUT voltage with buffer ON	-	-	V_{DDA} – 0.2	V	
DAC_OUT min(1)	Lower DAC_OUT voltage with buffer OFF	-	0.5	-	mV	It gives the maximum output excursion of the DAC.
DAC_OUT max(1)	Higher DAC_OUT voltage with buffer OFF	-	-	V_{DDA} – 1LSB	V	
I_{DDA}(1)	DAC DC current consumption in quiescent mode(2)	-	-	600	µA	With no load, middle code (0x800) on the input
		-	-	700	µA	With no load, worst code (0xF1C) on the input
DNL(3)	Differential non linearity Difference between two consecutive code-1LSB)	-	-	±0.5	LSB	Given for the DAC in 10-bit configuration
		-	-	±2	LSB	Given for the DAC in 12-bit configuration
INL(3)	Integral non linearity (difference between measured value at Code i and the value at Code i on a line drawn between Code 0 and last Code 1023)	-	-	±1	LSB	Given for the DAC in 10-bit configuration
		-	-	±4	LSB	Given for the DAC in 12-bit configuration
Offset(3)	Offset error (difference between measured value at Code (0x800) and the ideal value = V_{DDA}/2)	-	-	±10	mV	-
		-	-	±3	LSB	Given for the DAC in 10-bit at V_{DDA} = 3.6 V
		-	-	±12	LSB	Given for the DAC in 12-bit at V_{DDA} = 3.6 V

Figure 33. I²S master timing diagram (Philips protocol)



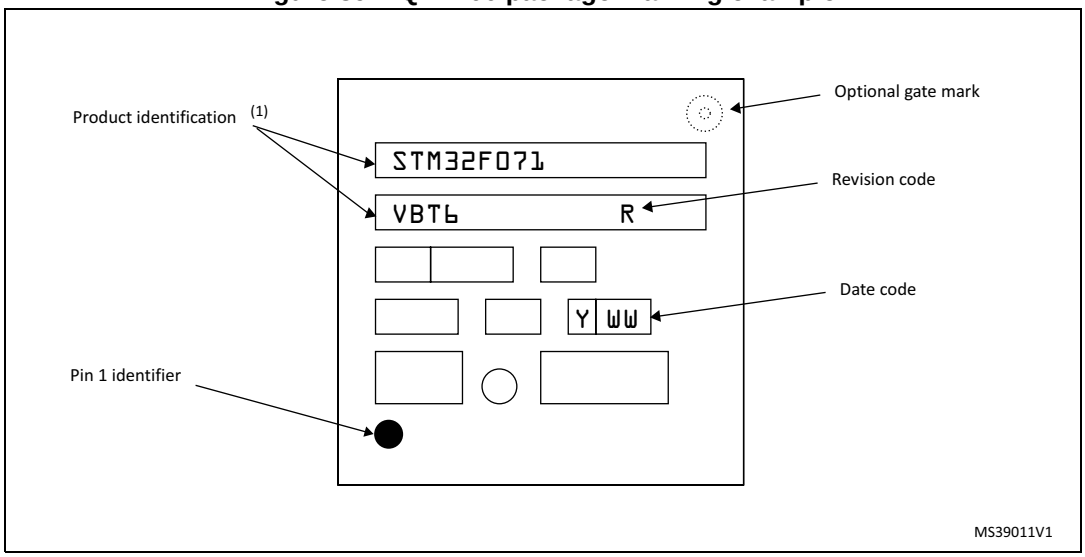
1. Data based on characterization results, not tested in production.
2. LSB transmit/receive of the previously transmitted byte. No LSB transmit/receive is sent before the first byte.

Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 39. LQFP100 package marking example



1. Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering Samples to run qualification activity.

As applications do not commonly use the STM32F071x8/xB at maximum dissipation, it is useful to calculate the exact power consumption and junction temperature to determine which temperature range will be best suited to the application.

The following examples show how to calculate the temperature range needed for a given application.

Example 1: High-performance application

Assuming the following application conditions:

Maximum temperature T_{Amax} = 82 °C (measured according to JESD51-2), I_{DDmax} = 50 mA, V_{DD} = 3.5 V, maximum 20 I/Os used at the same time in output at low level with I_{OL} = 8 mA, V_{OL}= 0.4 V and maximum 8 I/Os used at the same time in output at low level with I_{OL} = 20 mA, V_{OL}= 1.3 V

P_{INTmax} = 50 mA × 3.5 V= 175 mW

P_{IOmax} = 20 × 8 mA × 0.4 V + 8 × 20 mA × 1.3 V = 272 mW

This gives: P_{INTmax} = 175 mW and P_{IOmax} = 272 mW:

P_{Dmax}= 175 + 272 = 447 mW

Using the values obtained in *Table 77* T_{Jmax} is calculated as follows:

– For LQFP64, 45 °C/W

T_{Jmax} = 82 °C + (45 °C/W × 447 mW) = 82 °C + 20.115 °C = 102.115 °C

This is within the range of the suffix 6 version parts (–40 < T_J < 105 °C).

In this case, parts must be ordered at least with the temperature range suffix 6 (see *Section 8: Ordering information*).

Note: With this given P_{Dmax} we can find the T_{Amax} allowed for a given device temperature range (order code suffix 6 or 7).

Suffix 6: $T_{Amax} = T_{Jmax}$ - (45°C/W × 447 mW) = 105-20.115 = 84.885 °C

Suffix 7: $T_{Amax} = T_{Jmax}$ - (45°C/W × 447 mW) = 125-20.115 = 104.885 °C

Example 2: High-temperature application

Using the same rules, it is possible to address applications that run at high temperatures with a low dissipation, as long as junction temperature T_J remains within the specified range.

Assuming the following application conditions:

Maximum temperature T_{Amax} = 100 °C (measured according to JESD51-2), I_{DDmax} = 20 mA, V_{DD} = 3.5 V, maximum 20 I/Os used at the same time in output at low level with I_{OL} = 8 mA, V_{OL}= 0.4 V

P_{INTmax} = 20 mA × 3.5 V= 70 mW

P_{IOmax} = 20 × 8 mA × 0.4 V = 64 mW

This gives: P_{INTmax} = 70 mW and P_{IOmax} = 64 mW:

P_{Dmax} = 70 + 64 = 134 mW

Thus: P_{Dmax} = 134 mW

Using the values obtained in *Table 77* T_{Jmax} is calculated as follows:

– For LQFP64, 45 °C/W

T_{Jmax} = 100 °C + (45 °C/W × 134 mW) = 100 °C + 6.03 °C = 106.03 °C

Table 79. Document revision history (continued)

Date	Revision	Changes
17-Dec-2015	3 (continued)	***Section 6: Electrical characteristics***: – *Table 21: Voltage characteristics and Table 22: Current characteristics updated* – *Table 24: General operating conditions - added footnote for V_{IN} of TTa I/O* – *Table 28: Embedded internal reference voltage*: added t_{START} parameter and removal of -40°-to-85° condition for V_{REFINT} and associated note – *Table 32: Typical and maximum current consumption from the V_{BAT} supply - added max values* – *Merger of two tables into Table 33: Typical current consumption, code executing from Flash memory, running from HSE 8 MHz crystal* – *Table 35: Peripheral current consumption - APB peripheral total current consumption corrected* – *Table 40: LSE oscillator characteristics (f_{LSE} = 32.768 kHz) - V_{DD} replaced with V_{DDIOx}* – *Table 41: HSI oscillator characteristics and Figure 18: HSI oscillator accuracy characterization results for soldered parts updated* – *Table 42: HSI14 oscillator characteristics:* changed ACC_{HSI14} for 0-70° Ta range – *Table 46: Flash memory characteristics:* removed V_{prog} – *Table 49: EMI characteristics* updated – *Table 50: ESD absolute maximum ratings* updated – *Table 53: I/O static characteristics* - note removed – *Table 57: ADC characteristics* - updated some parameter values, test conditions and added footnotes (3) and (4) – *Table 60: DAC characteristics* - I_{DDA} max value (DAC DC current consumption) updated – *Table 61: Comparator characteristics* - min value added for V_{DDA} – *Figure 28: Maximum V_{REFINT} scaler startup time from power down* added – *Table 63: V_{BAT} monitoring characteristics:* changed the typical value for R parameter – *Table 69: I^2S characteristics*: table reorganized ***Section 7: Package information*:** – information on packages generally updated ***Section 8: Ordering information*:** – added tray packing to options
14-Jun-2016	4	Added STM32F071C8 part number ***Section 6: Electrical characteristics*:** – V_{REFINT} values updated in *Table 28: Embedded internal reference voltage* – R_{LOAD} - added value for connection to V_{DD}